



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

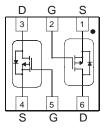
Features

- Low On-Resistance
 - $70m\Omega @V_{GS} = -4.5V$
 - $85m\Omega @V_{GS} = -2.5V$ •
 - 86mΩ (typ) $@V_{GS} = -1.8V$.
- Low Gate Threshold Voltage, -0.9V Max
- Fast Switching Speed
- Low Input/Output Leakage
- Low Profile, 0.5mm Max Height
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN2020B-6
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu annealed over Copper leadframe. • Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.0065 grams (approximate)

BOTTOM VIEW



TOP VIEW Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	PD	1.4	W
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	89	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

DFN2020B-6

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 1)	I _D	-3.8	A
Pulsed Drain Current (Note 4)	I _{DM}	-13	А

Device mounted on FR-4 PCB, on minimum recommended, 2oz Copper pad layout. 1.

2. No purposefully added lead.

Notes:

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Repetitive rating, pulse width limited by junction temperature. 3.

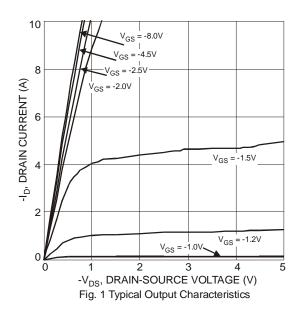
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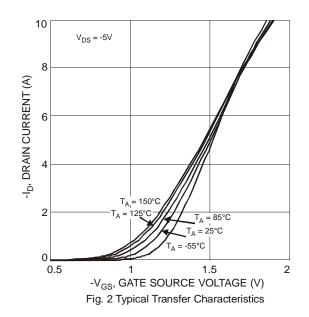


Electrical Characteristics @T_A = 25°C unless otherwise specified

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	-			•		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—		V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	IDSS			-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage				±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
Gale-Source Leakage	I _{GSS}			±800		$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)	-				-	
Gate Threshold Voltage	V _{GS(th)}	-0.45		-0.9	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
			54	70		$V_{GS} = -4.5V, I_D = -2.8A$
Static Drain-Source On-Resistance	R _{DS (ON)}		68	85	mΩ	V _{GS} = -2.5V, I _D = -2.0A
	- (-)		86	—		V _{GS} = -1.8V, I _D = -1.0A
Forward Transfer Admittance	Y _{fs}		8		S	V _{DS} = -5V, I _D = -2.8A
Diode Forward Voltage (Note 5)	V _{SD}		0.7	-1.2	V	V _{GS} = 0V, I _S = -1.6A
DYNAMIC CHARACTERISTICS						
Input Capacitance	Ciss		536		рF	
Output Capacitance	Coss	_	68		рF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		59	—	pF	1 = 1.00012
Gate Resistance	Rg	-	8.72	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	-	6.5	-	nC	
Gate-Source Charge	Q _{gs}	-	0.8	-	nC	$V_{GS} = -4.5V, V_{DD} = -10V,$
Gate-Drain Charge	Q _{qd}	-	1.4	-	nC	I _D = -1.5A
Turn-On Delay Time	t _{D(on)}	-	11.51	-	ns	
Turn-On Rise Time	tr	-	12.09	-	ns	$V_{GEN} = -4.5V, V_{DD} = -10V,$
Turn-Off Delay Time	t _{D(off)}	-	55.34	-	ns	$R_L = 10\Omega, R_G = 6\Omega$
Turn-Off Fall Time	t _f	-	27.54	-	ns	

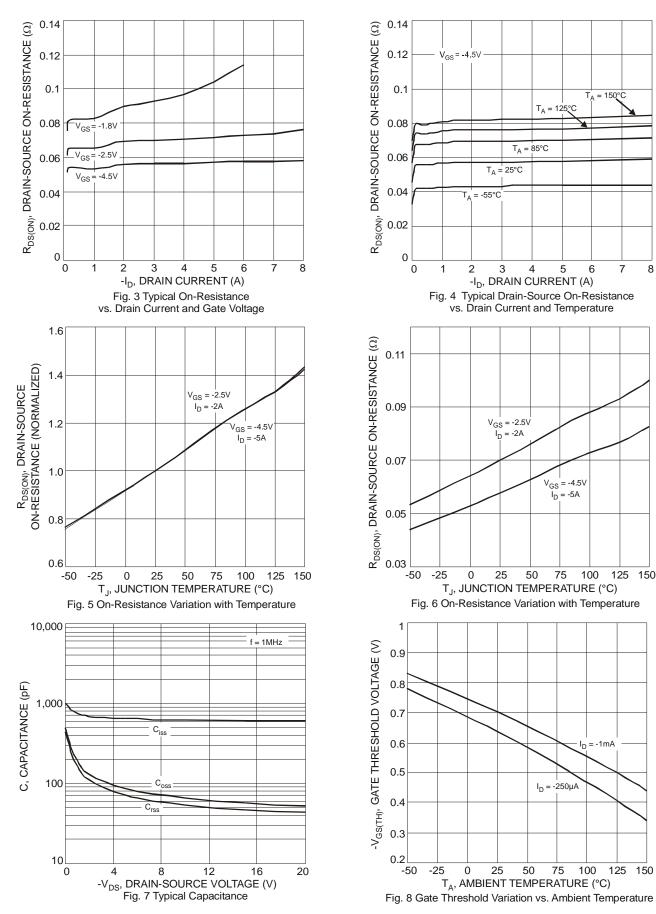
Notes: 5. Short duration pulse test used to minimize self-heating effect.



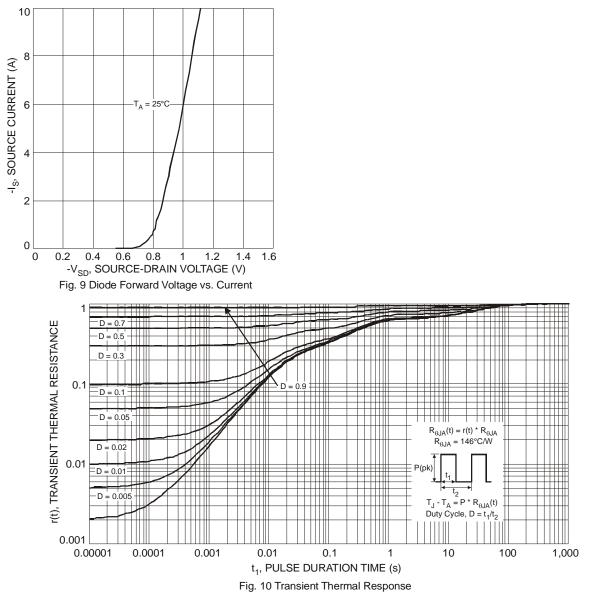


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Ordering Information (Note 6)

Part Number	Case	Packaging
DMP2160UFDB-7	DFN2020B-6	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

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P2 = Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)M = Month (ex: 9 = September) Dot denotes Pin 1

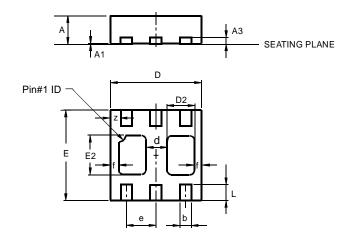
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Date Code Key			_
Year	2008	2009	20
Code	V	W	Х

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

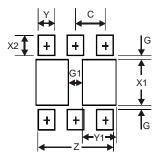


Package Outline Dimensions



DFN2020B-6										
Dim	Dim Min Max Typ									
Α	0.545	0.605	0.575							
A1	0	0.05	0.02							
A3			0.13							
b	0.20	0.30	0.25							
D	1.95	2.075	2.00							
d	_	_	0.45							
D2	0.50	0.70	0.60							
e — 0.65										
E 1.95 2.075 2.0										
E2	0.90	1.10	1.00							
f	_	_	0.15							
L	0.25	0.35	0.30							
z	_	_	0.225							
All Dimensions in mm										

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
С	0.65



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